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| Objective |
| Batch name: Process template |
| This process is a guideline on how to spin, develop and rinse CSAR62 on substrates as Si, SiO2 and SOI.CSAR is a semi chemically amplified e-beam resist. The resist has been approved to carry into DTU Danchip cleanroom, but this flow has not been tested or optimized. |

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| Step Heading | Equipment | **ZEP spinning on Si, SiO2, SOI** | Comments |
| 1. Pretreatment
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| * 1. Surface treatment
 | BHF dip *or*HMDS | BHF dip for Si substrates (30 sec, H2O 5 min) HMDS treatment for SiO2 and III-V substrates | Generally, pre-treatment is not recommended by ZEON.  |
| 1. Spin coat of CSAR
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| * 1. Coat wafers
 | Manual Spinner 1, or III-V spinner | **Resist:** CSAR (AR-P 6200-2, AllResist)**Spin:** XX sec @ YYYY rpm **Softbake:**  | Use filter on syringe when dispensing the resist. |
| 1. E-beam exposure
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 | E-beam writer | Dose: 200 - 350 µC/cm2; a dose-test is required. See e-beam logbook for inspiration. | Dose depends strongly on substrate material, thickness of resist, critical dimension and load of pattern. |
| 1. Development & Rinse
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| * 1. Develop-ment
 | Developer (E-beam) | Develop with X AR 600-54/6, use agitation.Rinse with H2O, blow dry with N2 | Dose depends on how you develop; make sure you develop in same manner as after dose-test. |
| 1. De-scum
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| * 1. De-scum
 | BHF dip | BHF dip for Si substrates (30 sec, H2O 5 min).(Never use plasma ash as de-scum, as such a process could generate particles on substrate). | De-scum generally not recommended. If residues appear, optimize dose, development and rinse process. |
| 1. Lift-off and Strip
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| * 1. Lift-off
 | Petribowl,Fumehood CR4 | Remover 1165 in petribowl. |  |